



QPA0001

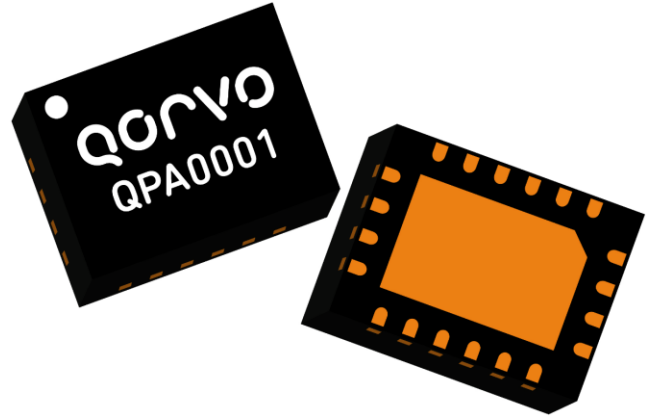
8.5 – 10.5 GHz 2W GaN Driver Amplifier

Product Description

Qorvo's QPA0001 is a packaged driver amplifier fabricated on Qorvo's 0.15 μm QGaN15 on SiC process. Operating from 8.5 to 10.5 GHz, the QPA0001 can deliver 2 W saturated output power, 50 % power-added efficiency and 27 dB of large signal gain.

QPA0001 incorporates active bias control to provide customers with bias point stability while reducing system complexity.

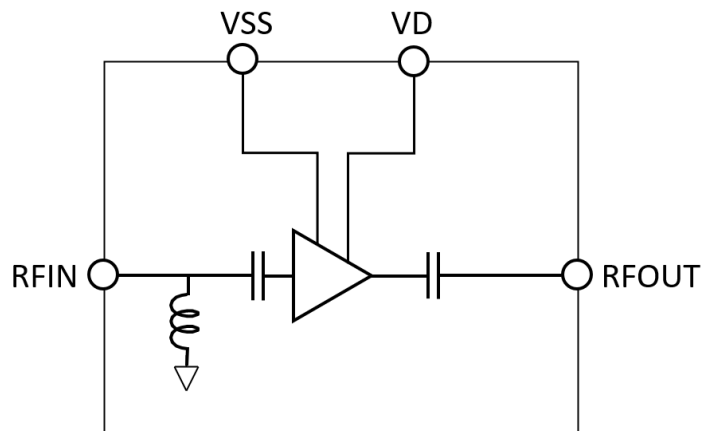
The QPA0001 is available in a 4x3 mm mold encapsulated QFN. With a compact size, it can support tight lattice spacing requirements for phased array radar applications.



Product Features

- Frequency Range: 8.5 – 10.5 GHz
- Small Signal Gain: 33 dB (mid-band)
- Pout: 33 dBm ($P_{\text{IN}} = 6$ dBm)
- Large Signal Gain: 27 dB (@ $P_{\text{in}} = 6$ dBm)
- PAE: 50 % Pulse Mode
- Input Return Loss: 12 dB
- Output Return Loss: 10 dB
- Harmonic: -20 dBc (@ $P_{\text{in}} = 6$ dBm)
- Active Bias Control: $V_D = 16$ V, $I_{DQ} = 55$ mA typical
- Package Dimensions: 4.0 x 3.0 x 0.65 mm

Functional Block Diagram



Applications

- Commercial and military radar
- Communications

Ordering Information

| Part No. | Description |
|--------------|---------------------------------|
| QPA0001 | Shipping Tray, Qty 50 |
| QPA0001TR7 | Tape and Reel 7", Qty 250 |
| QPA0001EVB01 | QPA0001 Evaluation Board, Qty 1 |

**QPA0001****8.5 – 10.5 GHz 2W GaN Driver Amplifier**

Recommended Operating Conditions

| Parameter | Min | Typ | Max | Units |
|---|------|-----------|------|-------|
| Drain Voltage (VD) | | 16 | | V |
| Drain Current (IDQ, self-bias, values are typical) | | 55 | | mA |
| Drain Current Under RF Drive | | See plots | | mA |
| Active Gate Control Voltage (Vss) | -3.3 | -3 | -2.7 | V |
| Active Gate Control Current Under RF Drive | | See plots | | mA |
| Temperature (T _{BASE}) | -40 | | +85 | °C |

Electrical performance is measured under conditions noted in the electrical specifications table. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

| Parameter ^{1, 3} | Min | Typ | Max | Units |
|--|-----|-------|------|-------|
| Operational Frequency Range | 8.5 | | 10.5 | GHz |
| Small Signal Gain | | 33 | | dB |
| Input Return Loss | | 12 | | dB |
| Output Return Loss | | 10 | | dB |
| Output Power (@ Pin = 6 dBm) ² | | 33 | | dBm |
| Power Added Efficiency (@ Pin = 6 dBm) ² | | 50 | | % |
| Large Signal Gain (@ Pin = 6 dBm) ² | | 27 | | dB |
| 2 nd Harmonic Suppression (@ Pin = 6 dBm) | | -20 | | dBc |
| 3 rd harmonic Suppression (@ Pin = 6 dBm) | | -35 | | dBc |
| Small Signal Gain Temperature Coefficient | | -0.15 | | dB/°C |

1 Test conditions unless otherwise noted: T_{BASE} = +25 °C, V_D = +16 V, IDQ = 55 mA typical, Vss = -3.0 V.

2. Power tested under pulse mode, PW = 100uS, DC = 10%.

3. Data de-embedded of fixture losses.

**QPA0001****8.5 – 10.5 GHz 2W GaN Driver Amplifier****Absolute Maximum Ratings**

| Parameter | Min Value | Max Value | Units |
|---|-----------|-----------|-------|
| Drain Voltage (VD) | - | 29.5 | V |
| Gate Voltage Range (Vss) | -4 | -2.5 | V |
| Drain Current (IDS) | - | 700 | mA |
| Active Gate Control Current (IVss) | - | 10 | mA |
| Input Power (PIN), CW, 50 Ω , 85 °C, | - | 30 | dBm |
| Input Power (PIN), CW, Output VSWR 3:1, 85 °C | - | 30 | dBm |
| Mounting Temperature (30 Seconds) | - | 260 | °C |
| Storage Temperature | -55 | 150 | °C |

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

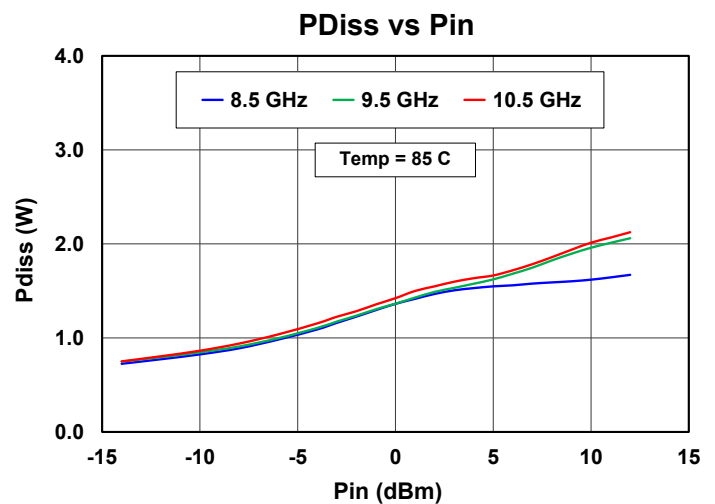
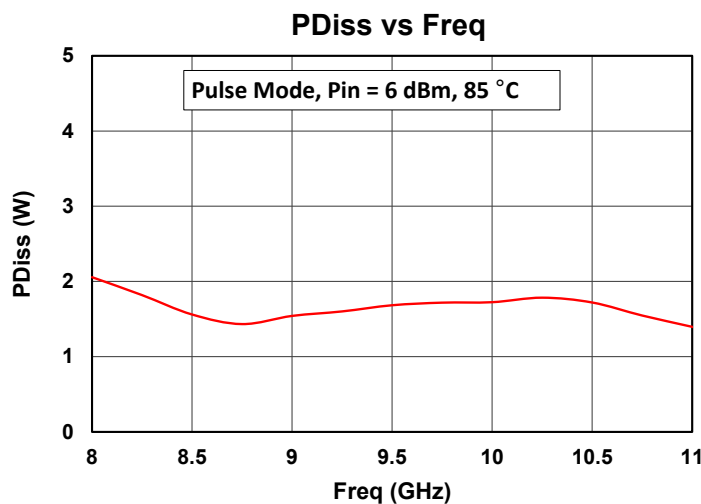
Thermal and Reliability Information

| Parameter | Values | Units | Conditions |
|--|--------|-------|---|
| Under Drive, Thermal Resistance (θ_{JC}) ^(1,2,3) | 11.4 | °C/W | T _{BASE} = 85 °C, V _D = +16 V, Pulse Mode, 100uS, 10% Freq = 10.25 GHz, IDS_DRIVE = 221 mA P _{IN} = +6 dBm, P _{OUT} = +32.4 dBm, P _{DISS} = 1.80 W |
| Channel Temperature (T _{CH}) ² | 105.5 | °C | |

Notes:

1. Thermal resistance is referenced to the package backside.
2. Base or ambient temperature is 85 °C, channel temperature is IR scan equivalent.
3. Refer to the following document for more information:

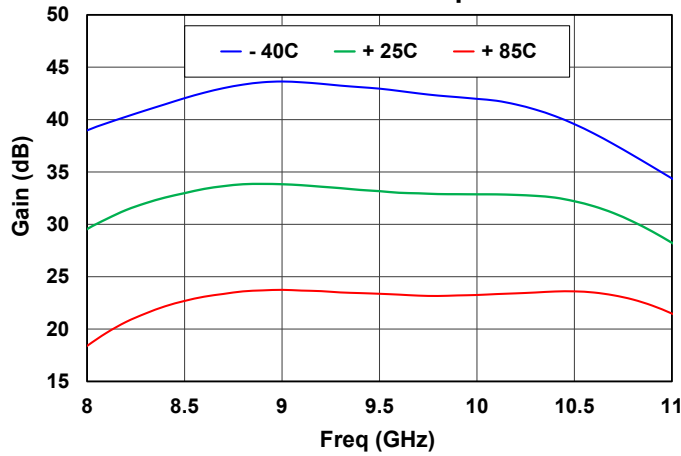
[GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)



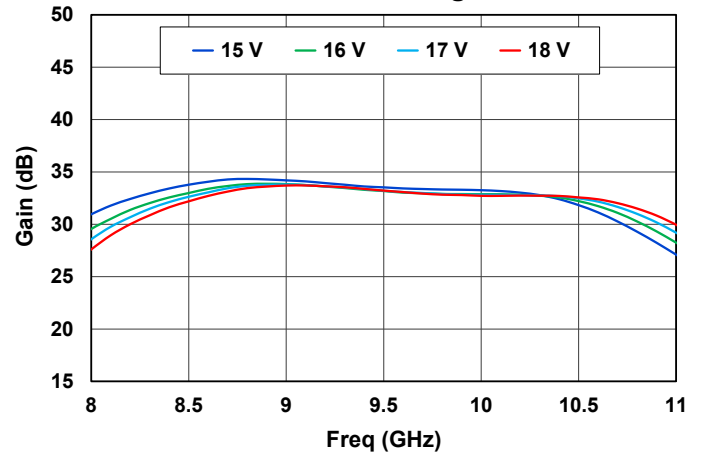
Performance Plots – Small Signal

Test conditions unless otherwise specified: $V_D = 16\text{ V}$, $V_{SS} = -3\text{ V}$, $25\text{ }^\circ\text{C}$

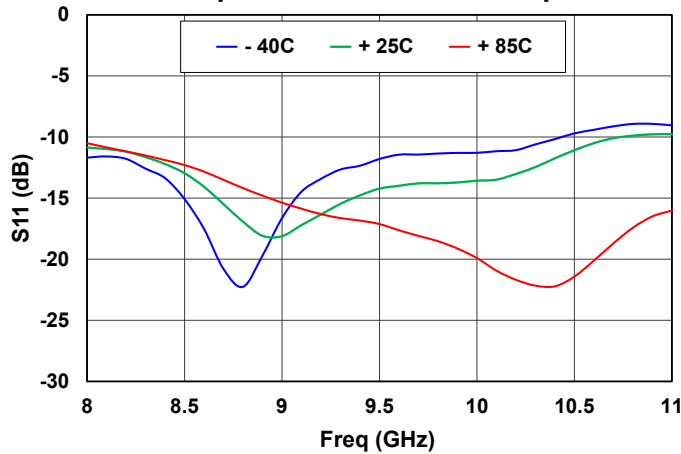
Gain vs Temp



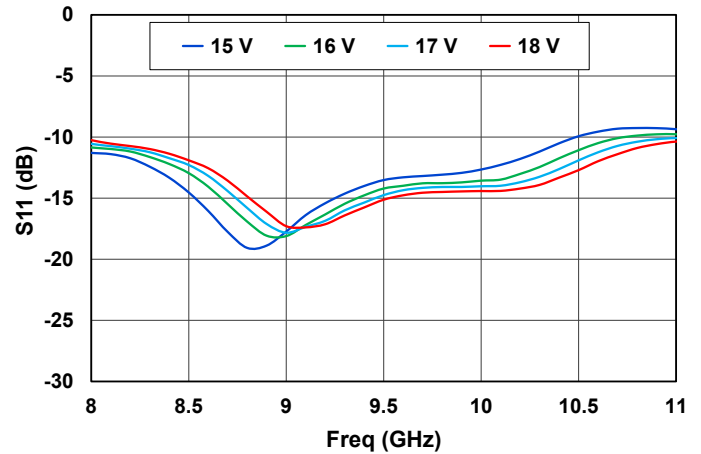
Gain vs Voltage



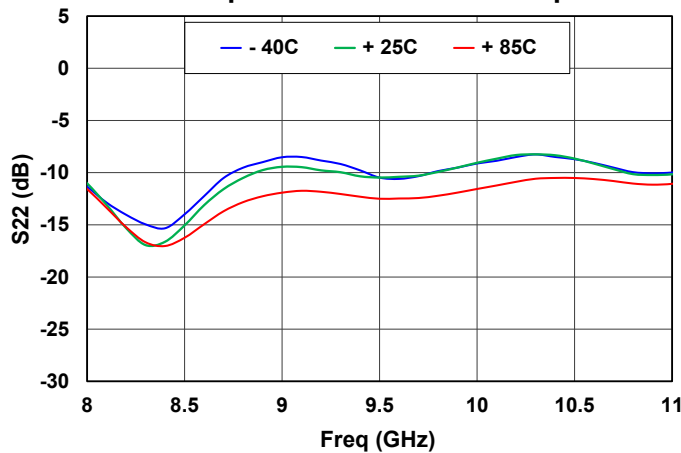
Input Return Loss vs Temp



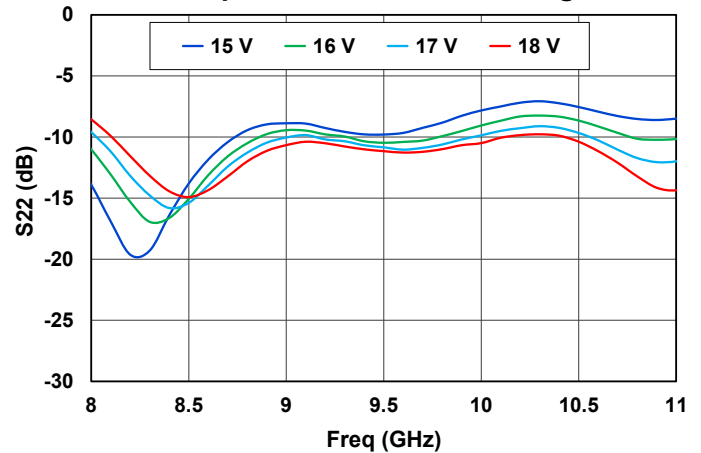
Input Return Loss vs Voltage



Output Return Loss vs Temp

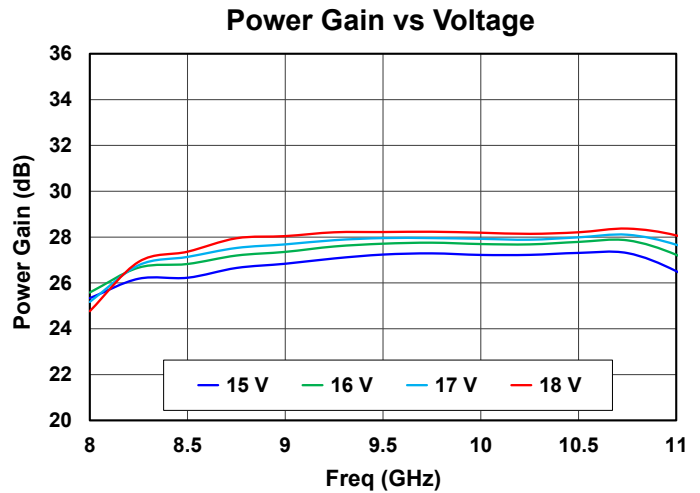
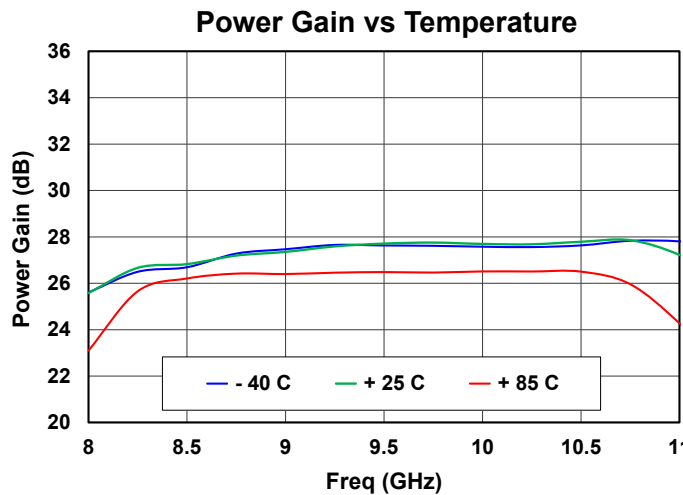
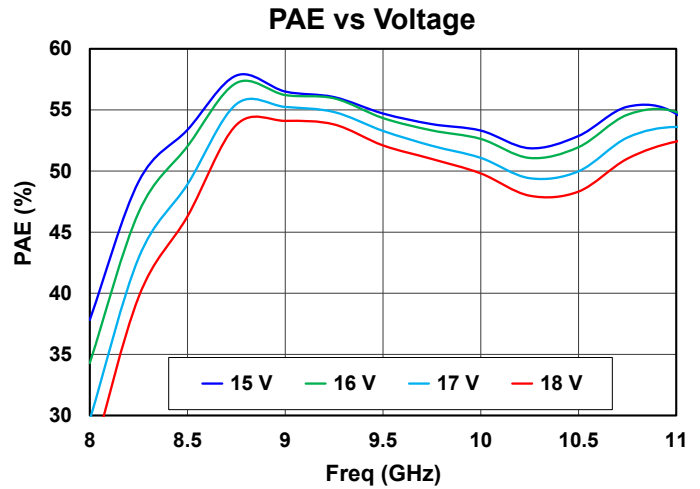
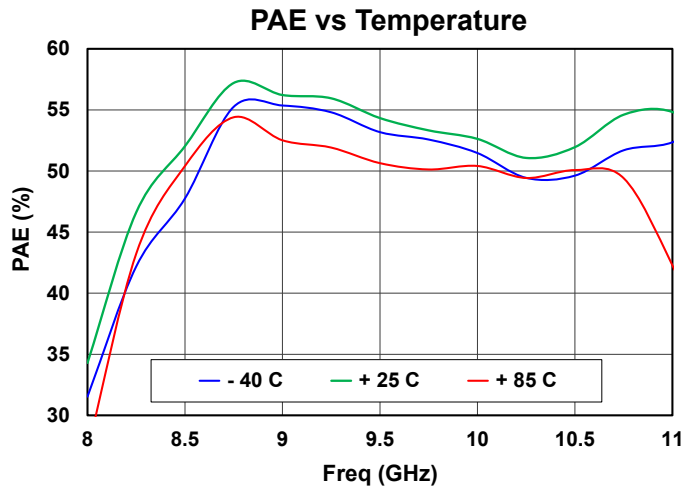
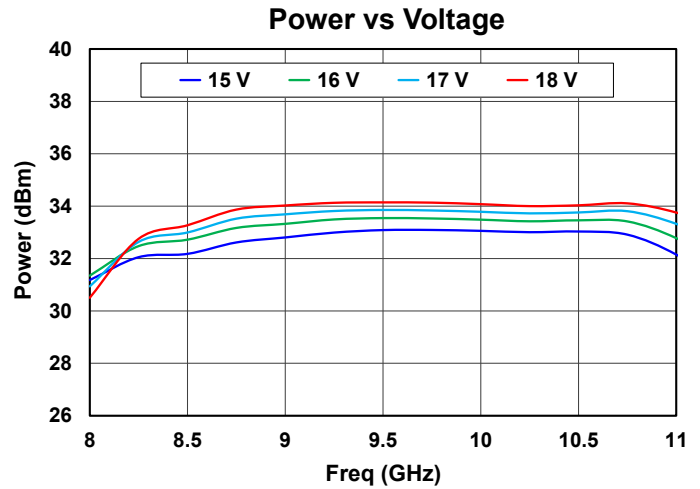
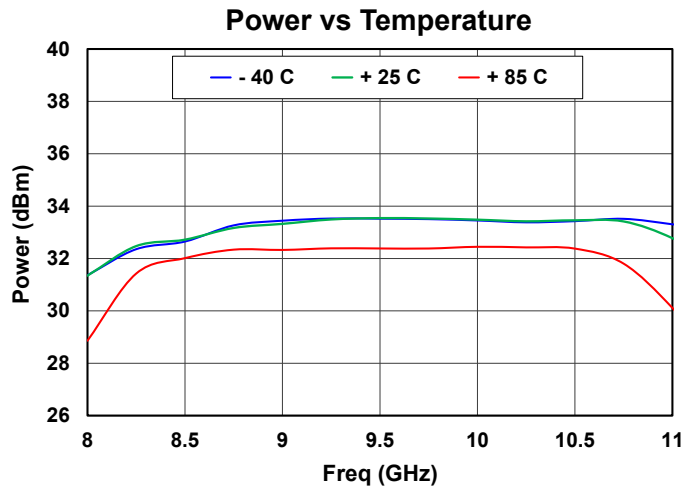


Output Return Loss vs Voltage



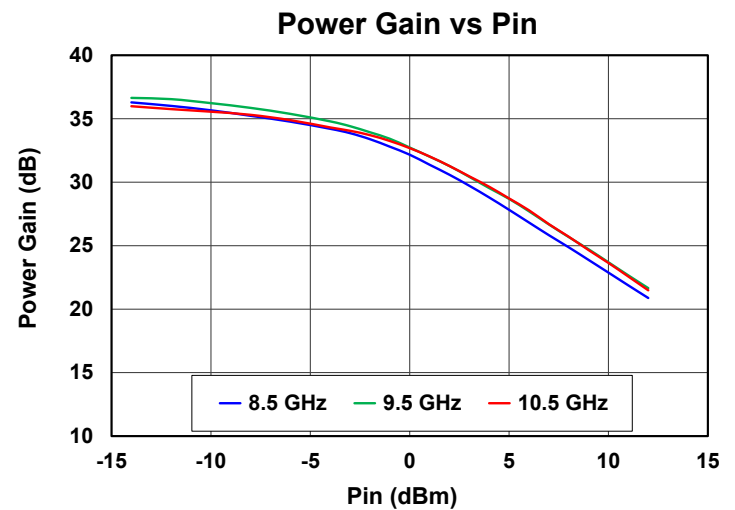
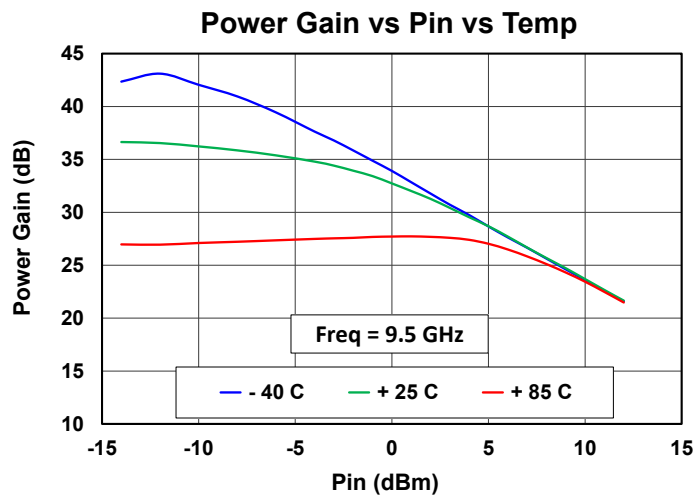
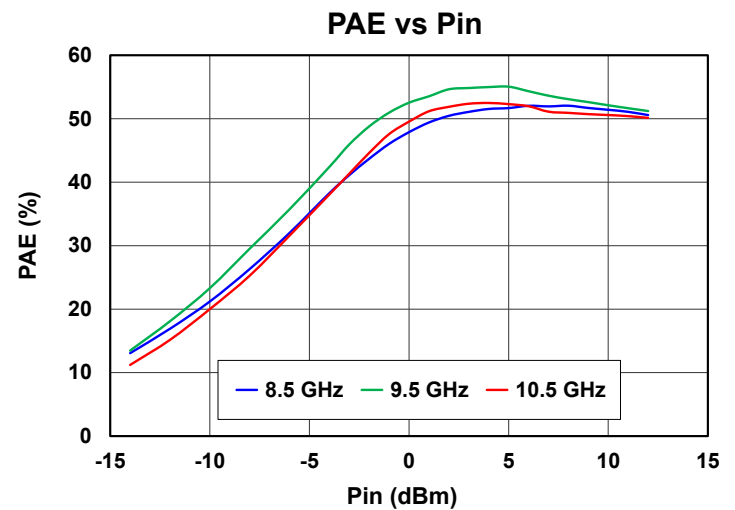
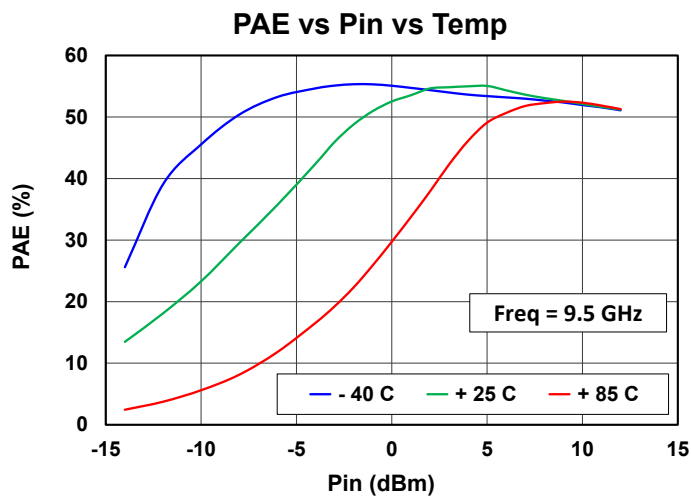
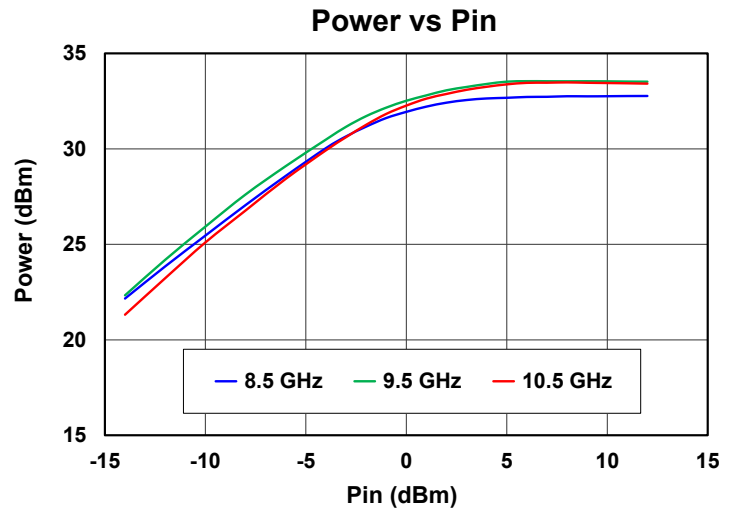
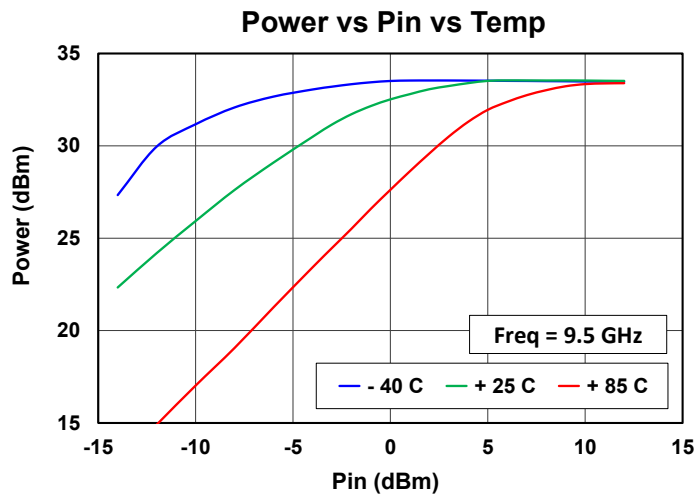
Performance Plots, Large Signal

Test Conditions unless otherwise stated: $V_D = 16\text{ V}$, $V_{SS} = -3\text{ V}$, Pulse Pin = 6 dBm, PW = 100 μs , DC = 10%, 25 °C



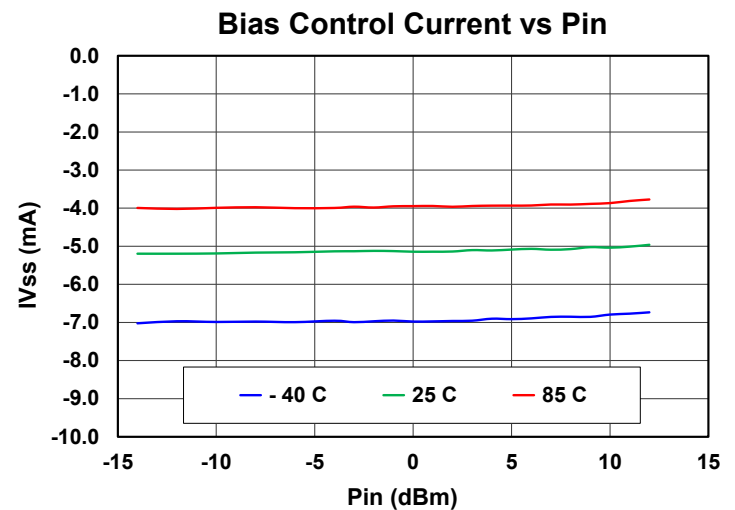
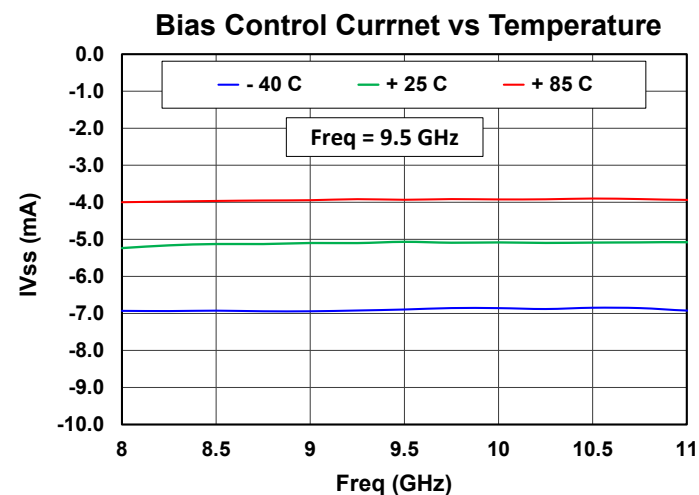
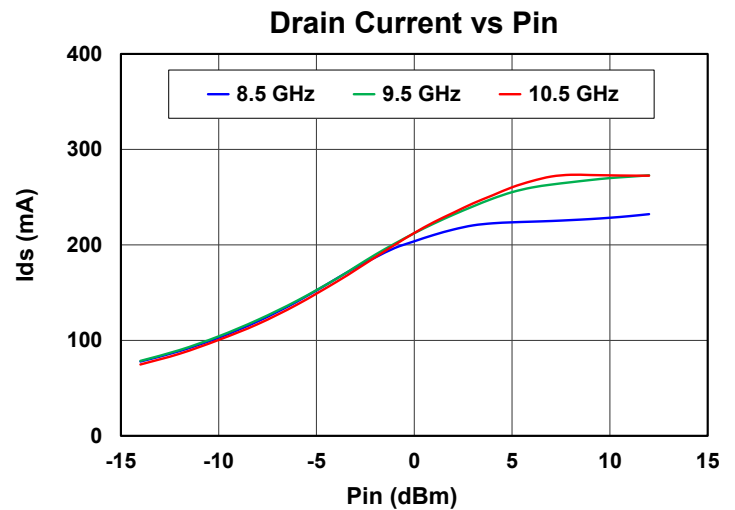
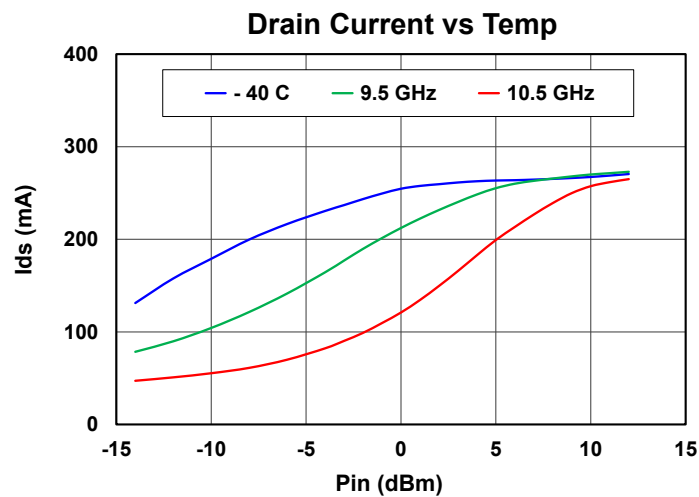
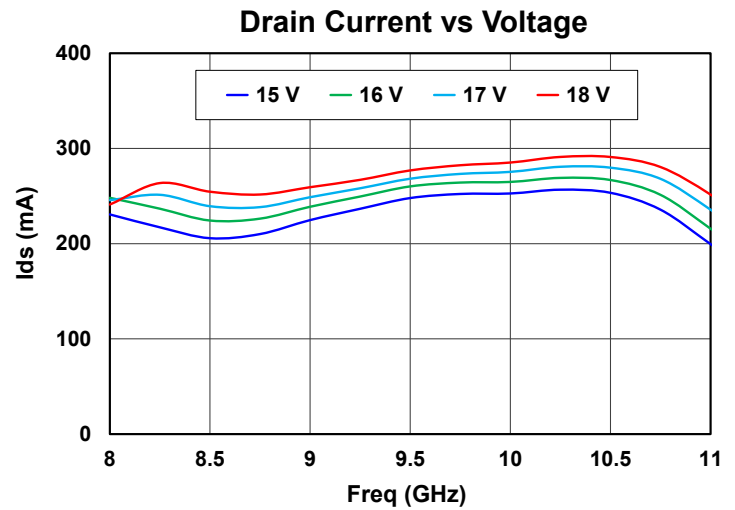
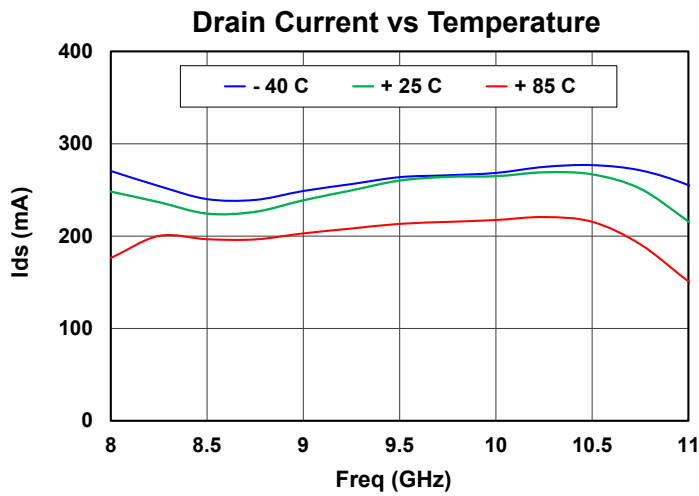
Power Sweep

Test Conditions unless otherwise stated: $V_D = 16\text{ V}$, $V_{SS} = -3\text{ V}$, Pulse Mode, $PW = 100\text{ }\mu\text{s}$, $DC = 10\%$, $25\text{ }^\circ\text{C}$



Power Sweep

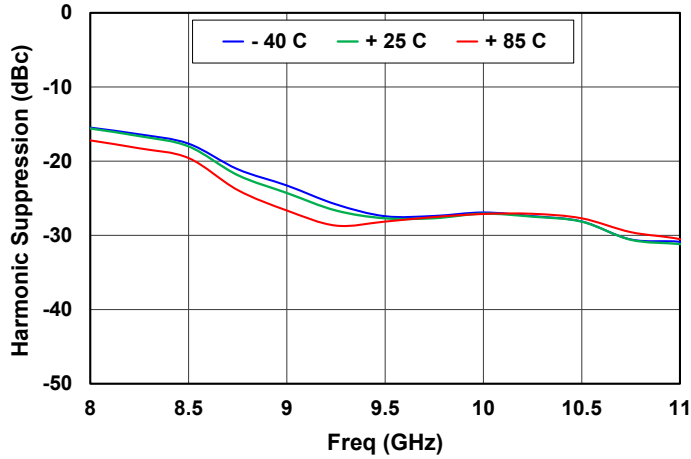
Test Conditions unless otherwise stated: $V_D = 16\text{ V}$, $V_{SS} = -3\text{ V}$, Pulse $P_{in} = 6\text{ dBm}$, $PW = 100\text{ }\mu\text{s}$, $DC = 10\%$, $25\text{ }^\circ\text{C}$



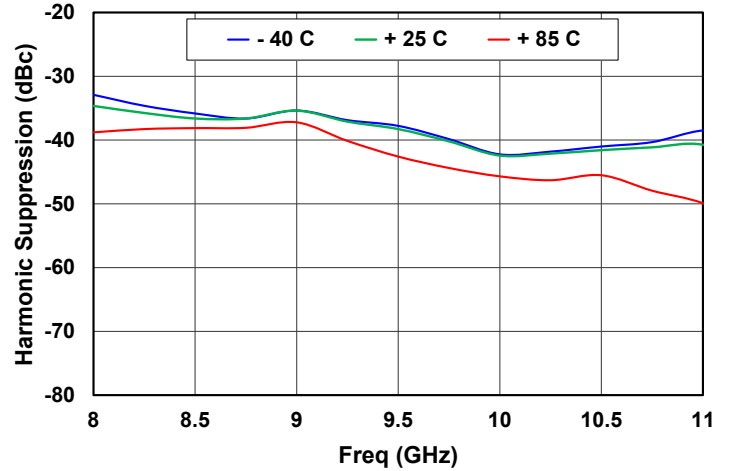
HarmonicSuppressions

Test Conditions unless otherwise stated: $V_D = 16\text{ V}$, $V_{SS} = -3\text{ V}$, Pulse $P_{in} = 6\text{ dBm}$, $PW = 100\text{ }\mu\text{s}$, $DC = 10\%$, $25\text{ }^\circ\text{C}$

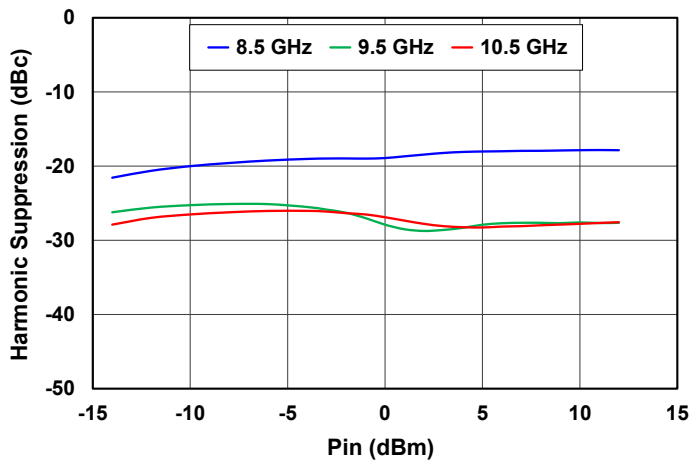
2nd Harmonic vs Temperature



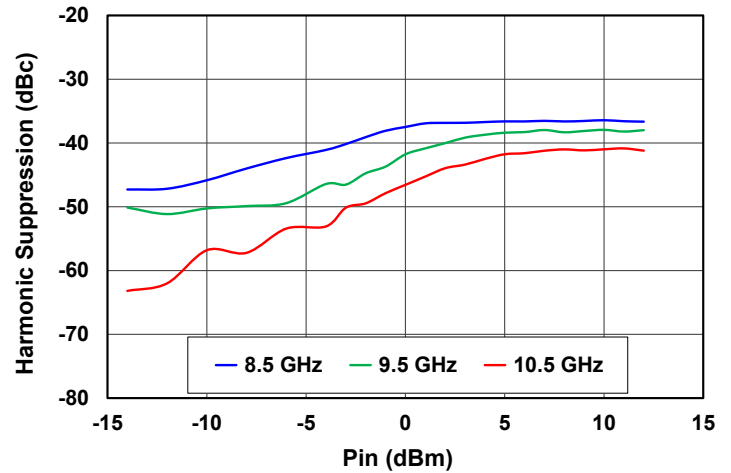
3rd Harmonic vs Temperature



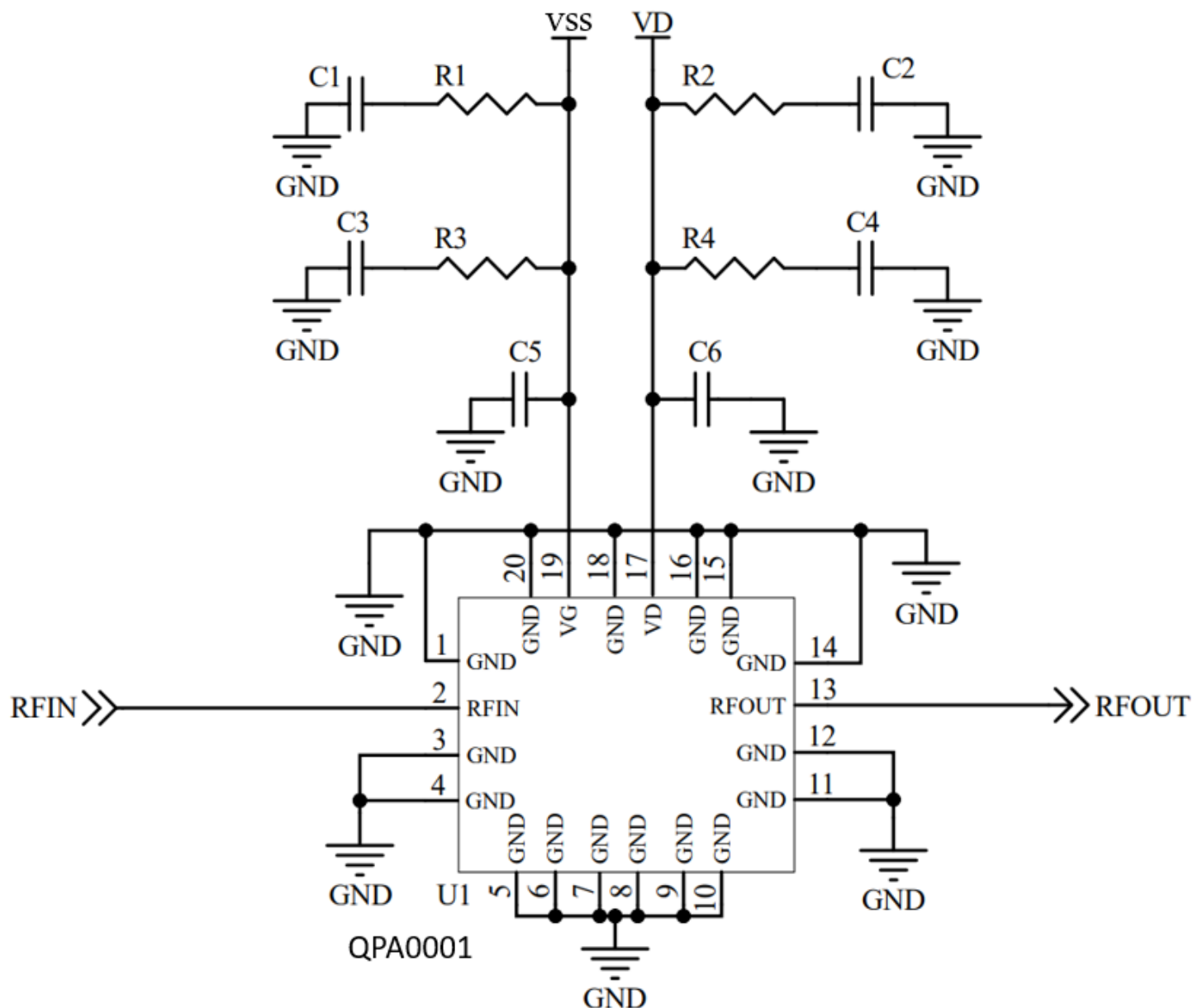
2nd Harmonic vs Pin



3rd Harmonic vs Pin



Application Circuit

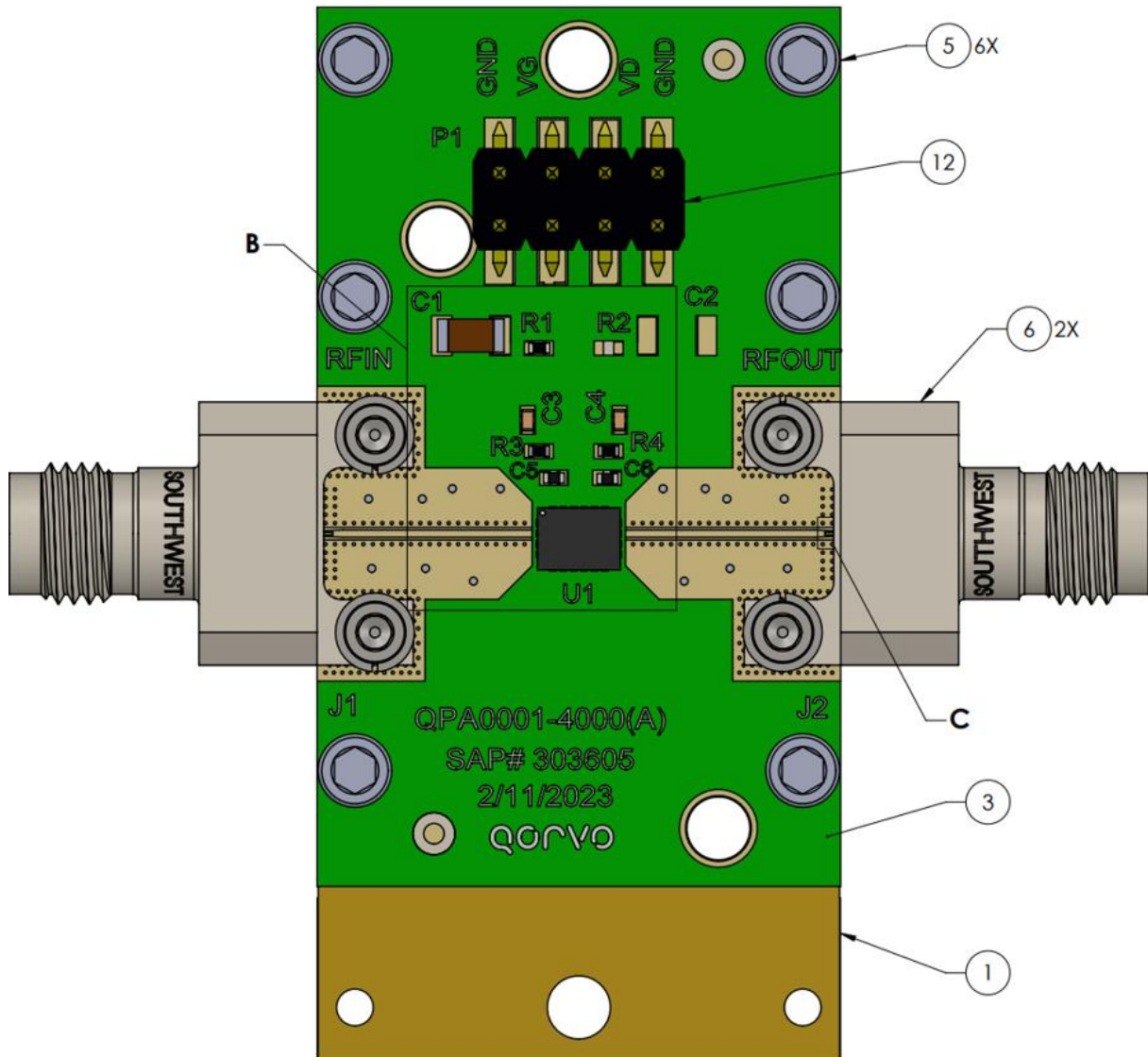


Bias Up Procedure

1. Set VD limit to 700 mA, Vss limit to 10 mA
2. Apply -3 V to Vss
3. Apply +16 V to VD, current should be around 55 mA
4. Turn on RF supply

Bias Down Procedure

1. Turn off RF supply
2. Turn off VD supply
3. Turn off Vss supply

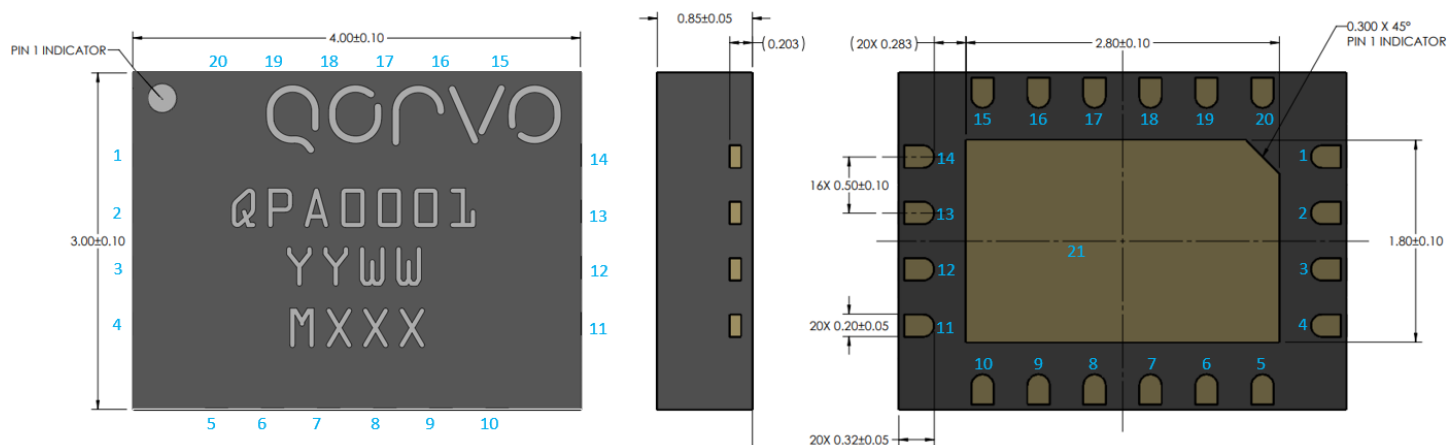


RF Layer is 0.008" thick Rogers Corp. RO4003C, $\epsilon_r = 3.38$. Metal layers are 0.5 oz. copper. The microstrip line at the connector interface is optimized for the Southwest Microwave end launch connector. Off-chip components not listed below are not populated, VG is connected to Vss.

Bill of Materials

| Reference Des. | Value | Description | Manuf. | Part Number |
|----------------|------------|----------------------------------|---------------------|-------------|
| C1 | 10 μ F | Cap, 10 uF, 1206, 50V, X5R, 20% | Various | |
| C5, C6 | 1000 pF | Cap, 1000pF, 0402, 50V, X7R, 10% | Various | |
| C3, C4 | 0.1 uF | Cap, 0.1 uF, 0402, 50V, X7R, 10% | Various | |
| R1 | 2 Ohms | Res, 2 Ohm, 0402, 1/16W, 5% | Various | |
| R3, R4 | 10 Ohms | Res, 10 Ohm, 0402, 1/10W, 5% | Various | |
| J1, J2 | - | CONN, 2.92mm, end launch, F. | Southwest Microwave | 1092-01A-12 |

Pin Configuration and Description



Dimensions in mm.

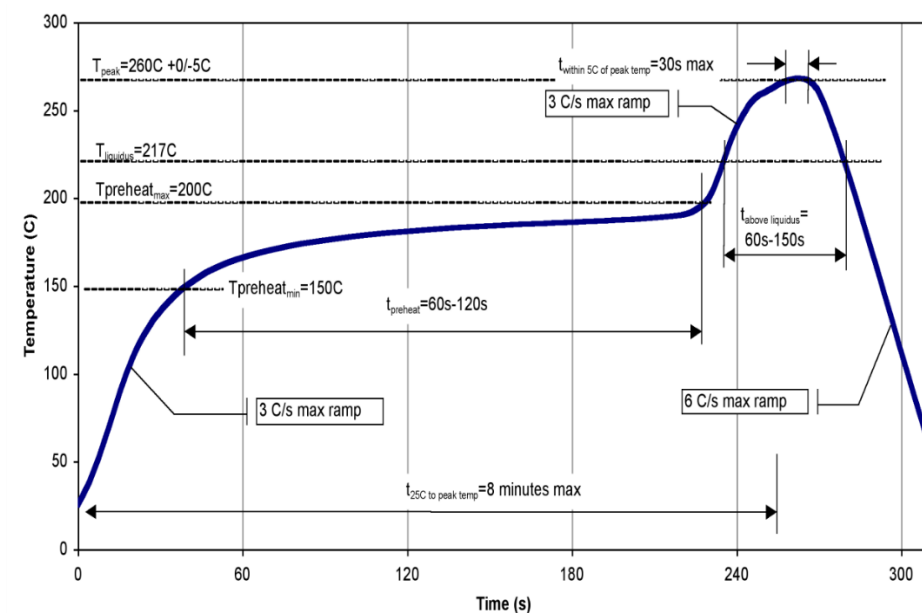
Package is mold encapsulated. Package lead finish is gold plated with typical gold thickness of 0.1 um
 Part Marking: QPA0001: Part Number, YY = Part Assembly Year, WW = Part Assembly Week, MXXX = Batch ID

| Pin No. | Label | Description |
|------------------------|-------|--|
| 1, 3-12, 14-16, 18, 20 | NC | No internal connections, can be grounded |
| 2 | RFIN | Input; matched to 50 Ω; DC grounded |
| 19 | Vss | Active gate control |
| 13 | RFOUT | Output; matched to 50 Ω; DC blocked |
| 17 | VD | Drain power supply |
| 21 | GND | Package base ground |

Solderability

- Compatible with the latest version of J-STD-020, Lead-free solder, 260 °C peak reflow temperature.

Recommended Soldering Temperature Profile



Handling Precautions

| Parameter | Rating | Standard |
|----------------------------------|--------|------------------------------------|
| ESD – Human Body Model (HBM) | 1C | ESDA / JEDEC JS-001-2012 |
| ESD – Charged Device Model (CDM) | C2b | ESDA / JEDEC JS-002-2014 |
| MSL – Convection Reflow 260 °C | 3 | JEDEC standard IPC/JEDEC J-STD-020 |



Caution!
ESD-Sensitive Device

RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.qorvo.com

Tel: 1-844-890-8163

Email: customer.support@qorvo.com

Important Notices

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